

FDS6575 Datasheet



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DiGi Electronics Part Number FDS6575-DG

Manufacturer onsemi

Manufacturer Product Number FDS6575

Description MOSFET P-CH 20V 10A 8SOIC

Detailed Description P-Channel 20 V 10A (Ta) 2.5W (Ta) Surface Mount 8

-SOIC



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FDS6575	onsemi
Series:	Product Status:
PowerTrench®	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	10A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
2.5V, 4.5V	13mOhm @ 10A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.5V @ 250µA	74 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	4951 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	2.5W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-SOIC	8-SOIC (0.154", 3.90mm Width)
Base Product Number:	
FDCCE	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



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September 2001

FDS6575

P-Channel 2.5V Specified PowerTrench MOSFET

General Description

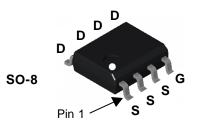
This PChannel 2.5V specified MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 8V).

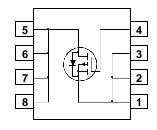
Applications

- · Power management
- · Load switch
- Battery protection

Features

- -10 A, -20 V. $R_{DS(ON)} = 13 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 17 \text{ m}\Omega$ @ $V_{GS} = -2.5 \text{ V}$
- · Low gate charge
- High performance trench technology for extremely low $R_{\text{DS(ON)}}$
- High current and power handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

<u></u>				
Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-10	А
	- Pulsed		-50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.5	
		(Note 1c)	1.2	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C

Thermal Characteristics

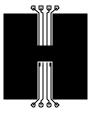
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	125	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

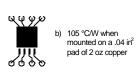
Device Marking	Device	Reel Size	Tape width	Quantity
FDS6575 FDS6575		13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-13		mV/°C
loss	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
Igssf	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -9 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}, T_J = 125 ^{\circ}\text{C}$		8.5 11 11	13 17 20	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-50			Α
G FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -10 \text{ A}$		57		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		4951		pF
Coss	Output Capacitance	f = 1.0 MHz		884		pF
C _{rss}	Reverse Transfer Capacitance			451		pF
Switchin	g Characteristics (Note 2)			•		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10V$, $I_{D} = -1 A$,		16	29	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t _{d(off)}	Turn-Off Delay Time			196	314	ns
t _f	Turn-Off Fall Time			78	125	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -10 \text{ A},$		53	74	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		6		nC
Q _{gd}	Gate-Drain Charge			12		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings			•	
ls	Maximum Continuous Drain–Source	Ţ			-2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2.1 \text{ A} \text{(Note 2)}$		-0.6	-1.2	V

1. R ALA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50 °C/W when mounted on a 1in² pad of 2 oz copper





c) 125 °C/W when mounted on a minimum pad.



2. Pulse Test: Pulse Width $< 300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

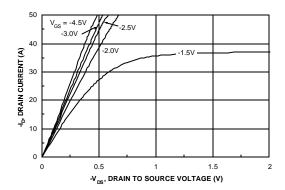


Figure 1. On-Region Characteristics.

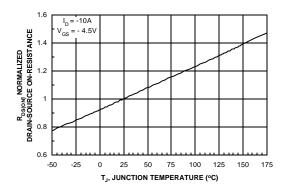


Figure 3. On-Resistance Variation with Temperature.

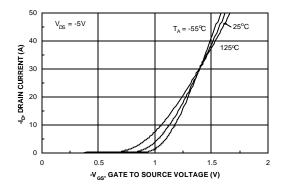


Figure 5. Transfer Characteristics.

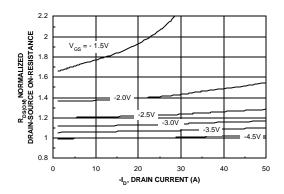


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

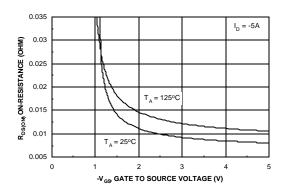


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

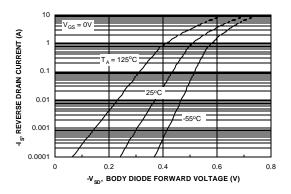
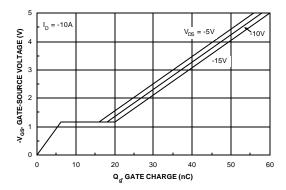


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



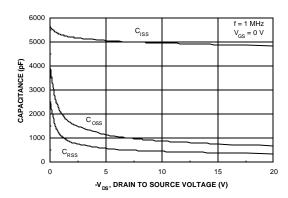
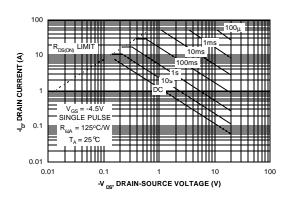


Figure 7. Gate Charge Characteristics.





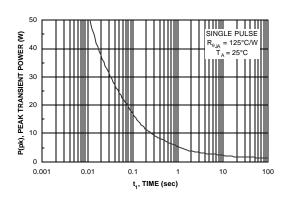


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

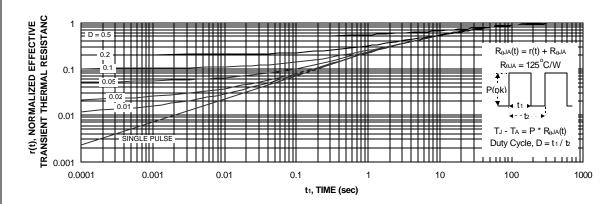


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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